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Team Nexperia

74HC1G86-Q100; 74HCT1G86-Q100

2-input EXCLUSIVE-OR gate

Rev. 2 — 16 December 2013 Product data sheet

1. General description

The 74HC1G86 is a single 2-input EXCLUSIVE-OR gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Input levels:
  - For 74HC1G86-Q100: CMOS level
  - For 74HCT1G86-Q100: TTL level
- Complies with JEDEC standard no. 7 A
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC1G86GW-Q100	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HCT1G86GW-Q100				
74HC1G86GV-Q100	−40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74HCT1G86GV-Q100				

4. Marking

Table 2. Marking codes

Type number	Marking[1]
74HC1G86GW-Q100	HH
74HCT1G86GW-Q100	TH
74HC1G86GV-Q100	H86
74HCT1G86GV-Q100	T86

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

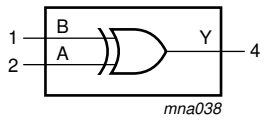


Fig 1. Logic symbol

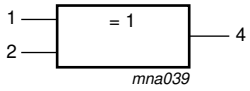


Fig 2. IEC logic symbol

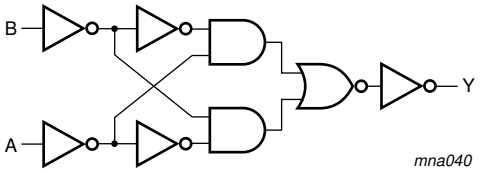


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

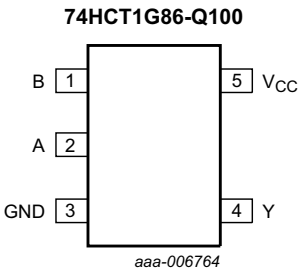


Fig 4. Pin configuration

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
A	**B**	**Y**
L	L	L
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±12.5	mA
I_{CC}	supply current			-	25	mA
I_{GND}	ground current			−25	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2]	-	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C, the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G86-Q100			74HCT1G86-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	+25	+125	−40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HC1G86-Q100								
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	V
		I_O = −2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
		I_O = −2.6 mA; V_{CC} = 6.0 V	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	V
		I_O = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I_O = 2.6 mA; V_{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	1.0	-	1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	10	-	20	μA
C_I	input capacitance		-	1.5	-	-	-	pF

Table 7. Static characteristics *...continued*

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HCT1G86-Q100								
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I_O = –2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I_O = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	1.0	-	1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; V_{CC} = 4.5 V to 5.5 V; V_I = V_{CC} – 2.1 V; I_O = 0 A	-	-	500	-	850	μA
C_I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; t_r = t_f ≤ 6.0 ns; All typical values are measured at T_{amb} = 25 °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	
For type 74HC1G86-Q100									
t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		V_{CC} = 2.0 V; C_L = 50 pF		-	22	115	-	135	ns
		V_{CC} = 4.5 V; C_L = 50 pF		-	11	23	-	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	9	-	-	-	ns
		V_{CC} = 6.0 V; C_L = 50 pF		-	9	20	-	23	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC}	[2]	-	23	-	-	-	pF

Table 8. Dynamic characteristics *…continued*

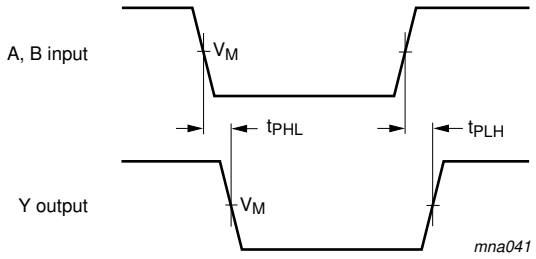
GND = 0 V; $t_r = t_f \leq 6.0$ ns; All typical values are measured at T_{amb} = 25 °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	
For type 74HCT1G86-Q100									
t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		V_{CC} = 4.5 V; C_L = 50 pF		-	13	23	-	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	10	-	-	-	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC} − 1.5 V	[2]	-	23	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

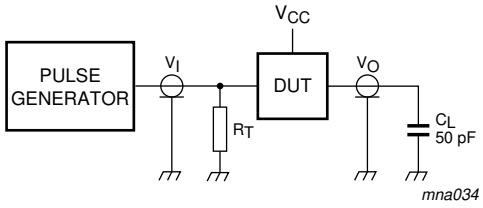
[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz
f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
$\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

12. Waveforms



For 74HC1G86-Q100: $V_M = 0.5 \times V_{CC}$; V_I = GND to V_{CC}.
For 74HCT1G86-Q100: V_M = 1.3 V; V_I = GND to 3.0 V.

Fig 5. The input (A and B) to output (Y) propagation delays

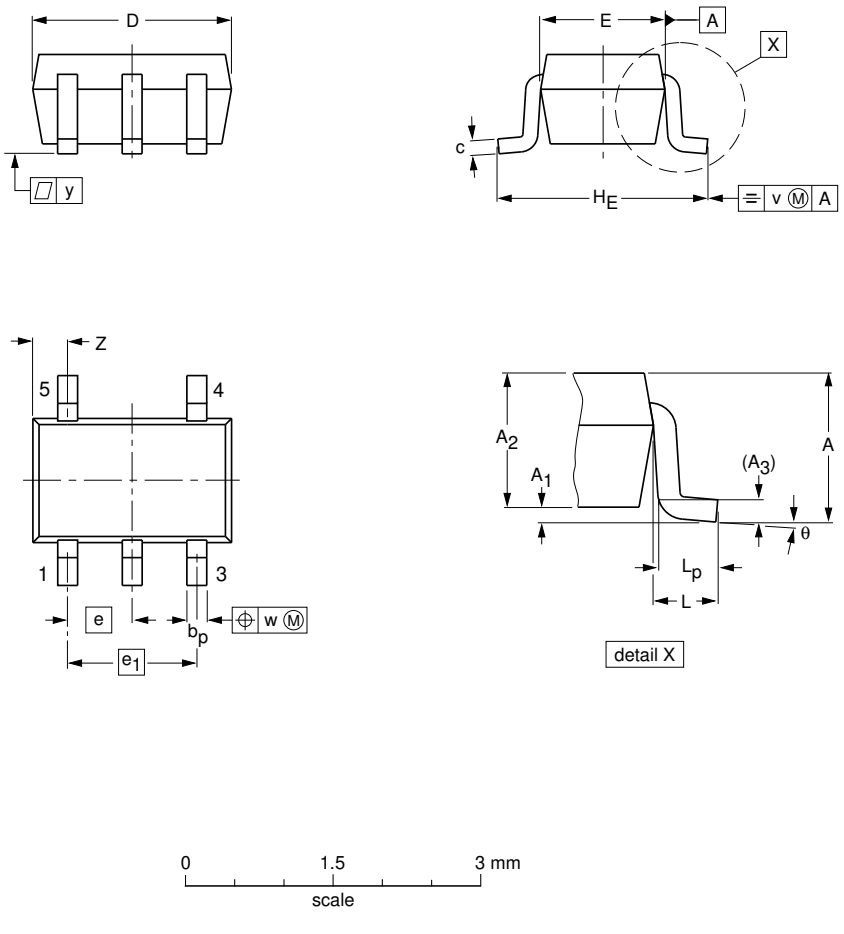


Test data is given in Table 8. Definitions for test circuit:
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Test circuit for measuring switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	e_1	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

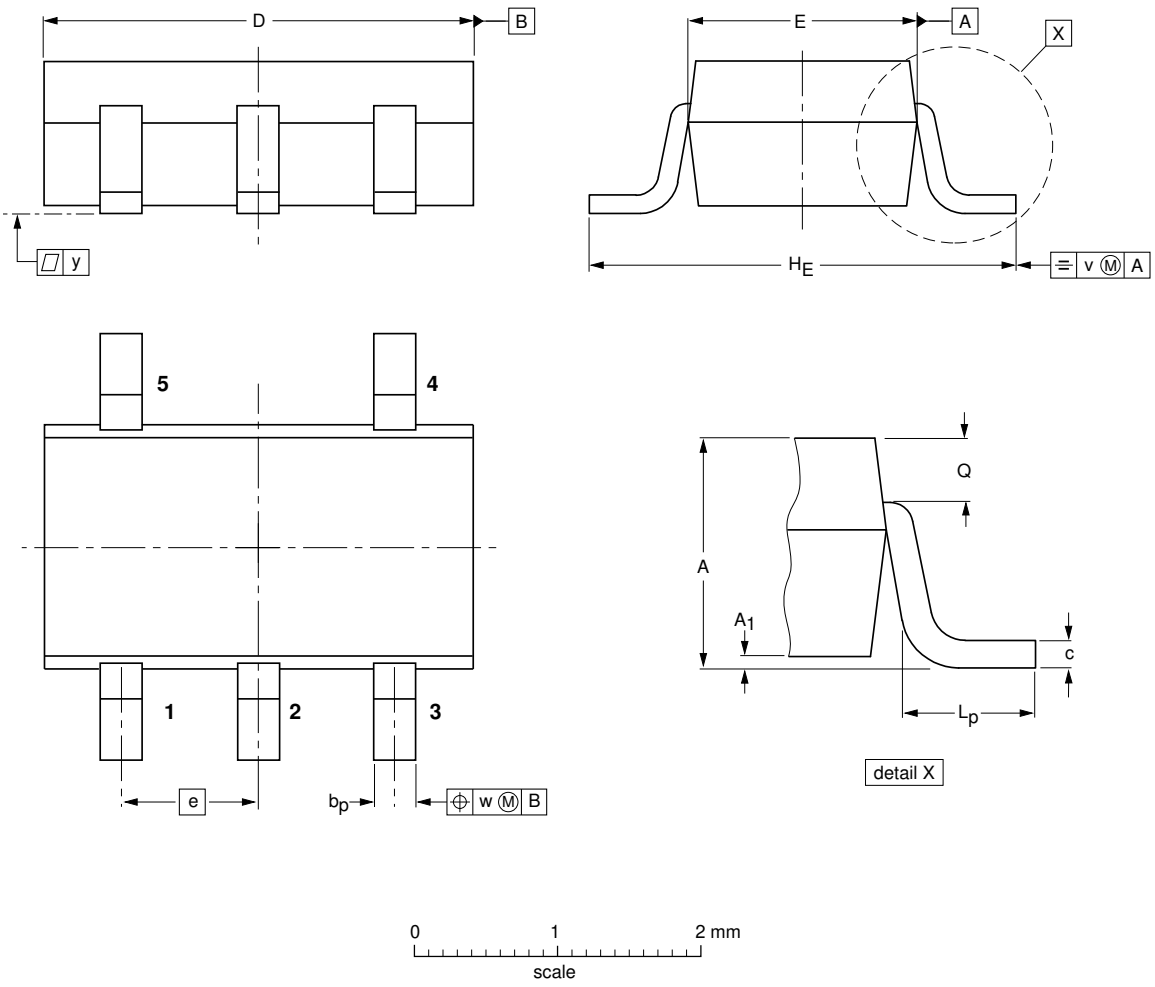
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads **SOT753**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G86_Q100 v.2	20131216	Product data sheet	-	74HC_HCT1G86_Q100 v.1
Modifications:	• Features and benefits updated (errata).			
74HC_HCT1G86_Q100 v.1	20130326	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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18. Contents

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Date of release: 16 December 2013
Document identifier: 74HC_HCT1G86_Q100